

ZERO BIAS SCHOTTKY DIODE

DESCRIPTION:

The **ASI 3486** is a Silicon Schottky Barrier Diode Designed for High Sensitivity Zero Bias Detector Applications up to 10 GHz.

FEATURES INCLUDE:

- Replacement for **HSCH3486** and **MA4E928** series
- -56 dBm T_{SS} Typical @ 10 GHz
- Hermetic Glass Package

MAXIMUM RATINGS

I_F	10 mA
V_R	2.0 V
P_{DISS}	300 mW @ T _C = 25 °C
T_J	-65 °C to +150 °C
T_{STG}	-65 °C to +150 °C
T_{soldering}	+230 °C for 5 Seconds

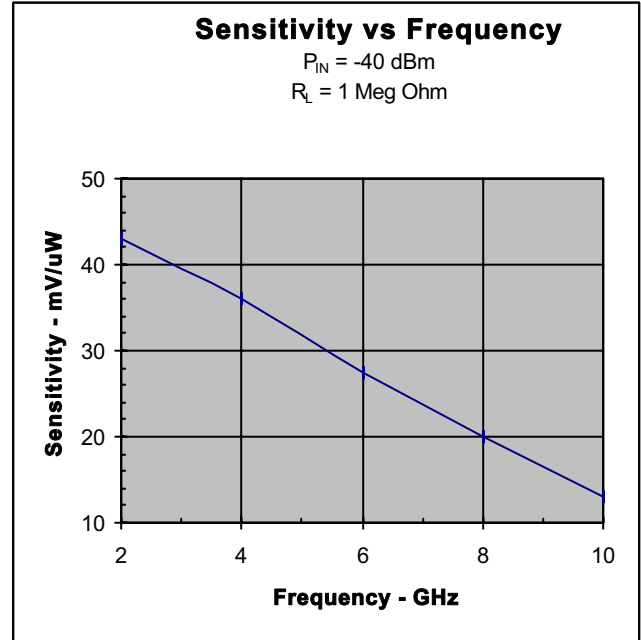
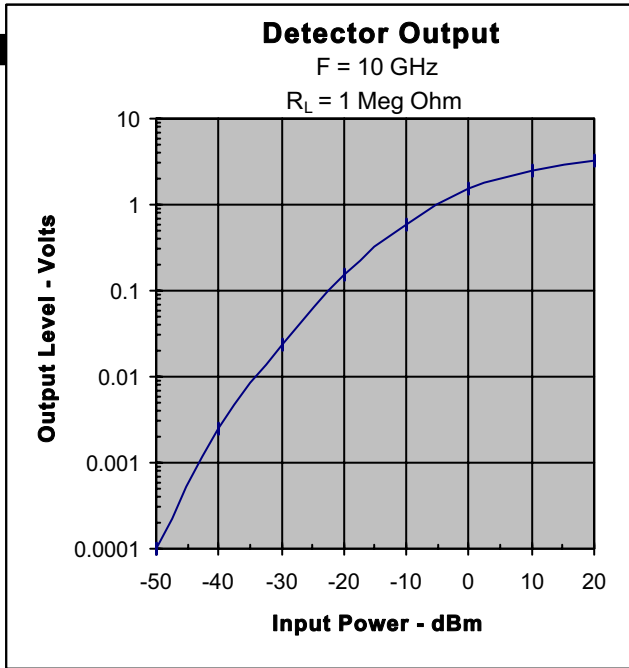


CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

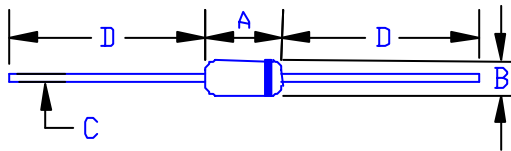
SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
V_F	I _F = 1.0 mA			185	225	mV
V_{BR}	I _R = 200 μA		0.8			V
C_{T0}	V _R = 0 V	f = 1.0 MHz		0.4		pF
T_{SS}	B _W = 2.0 MHz	f = 10 GHz	-54			dBm
γ	P _{IN} = -40 dBm	f = 10 GHz	7.5			mV/μW
R_v	P _{IN} = -40 dBm	f = 10 GHz	2.0		8.0	K Ohms

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DYNAMIC CHARACTERISTICS



PACKAGE OUTLINE



Body Color: Clear

STYLE 01		
	MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.150/3.81	.170/4.318
B	.068/1.727	.076/1.930
C	.014/.356	.020/.508
D	1.00/25.4	
E	CP=.027pF	
F	Lp=2.5nH	
G		

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